



THE DATASHEET OF IPD50R520CPATMA1



CoolMOS™ Power Transistor
Package

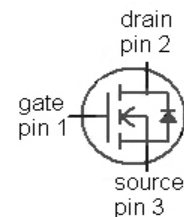
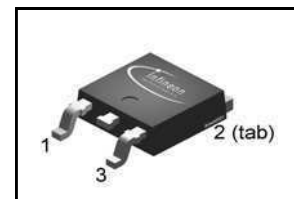
- Lowest figure of merit $R_{ON} \times Q_g$
- Ultra low gate charge
- Extreme dv/dt rated
- High peak current capability
- Pb-free lead plating; RoHS compliant; available in Halogen free mold compound^{a)}
- Fully qualified according to JEDEC for industrial applications

Product Summary

$V_{DS} @ T_{jmax}$	550	V
$R_{DS(on),max}$	0.520	Ω
$Q_{g,typ}$	13	nC

CoolMOS CP is designed for:

- Hard- & Softswitching SMPS topologies
- DCM PFC for Lamp ballast
- PWM for Lamp Ballast, PDP and LCD TV


PG-TO252


Type	Package	Marking
IPD50R520CP	PG-TO252	5R520P

Maximum ratings, at $T_j=25\text{ }^\circ\text{C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous drain current	I_D	$T_C=25\text{ }^\circ\text{C}$	7,1	A
		$T_C=100\text{ }^\circ\text{C}$	4,5	
Pulsed drain current ²⁾	$I_{D,pulse}$	$T_C=25\text{ }^\circ\text{C}$	15	
Avalanche energy, single pulse	E_{AS}	$I_D=2.5\text{ A}, V_{DD}=50\text{ V}$	166	mJ
Avalanche energy, repetitive $t_{AR}^{2),3)}$	E_{AR}	$I_D=2.5\text{ A}, V_{DD}=50\text{ V}$	0,25	
Avalanche current, repetitive $t_{AR}^{2),3)}$	I_{AR}		2,5	A
MOSFET dv/dt ruggedness	dv/dt	$V_{DS}=0\dots 400\text{ V}$	50	V/ns
Gate source voltage	V_{GS}	static	± 20	V
		AC ($f > 1\text{ Hz}$)	± 30	
Power dissipation	P_{tot}	$T_C=25\text{ }^\circ\text{C}$	66	W
Operating and storage temperature	T_j, T_{stg}		-55 ... 150	$^\circ\text{C}$

^{a)} non-Halogen free (OPN: IPD50R520CPBT); Halogen free (OPN: IPD50R520CPAT)

Maximum ratings, at $T_j=25\text{ °C}$, unless otherwise specified

Parameter	Symbol	Conditions	Value	Unit
Continuous diode forward current	I_S	$T_C=25\text{ °C}$	3,8	A
Diode pulse current ²⁾	$I_{S,pulse}$		15	
Reverse diode dv/dt ⁴⁾	dv/dt		15	V/ns

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	

Thermal characteristics

Thermal resistance, junction - case	R_{thJC}		-	-	1,9	K/W
Thermal resistance, junction - ambient	R_{thJA}	leaded	-	-	62	
Soldering temperature, wavesoldering only allowed at leads	T_{sold}	1.6 mm (0.063 in.) from case for 10 s	-	-	260	°C

Electrical characteristics, at $T_j=25\text{ °C}$, unless otherwise specified
Static characteristics

Drain-source breakdown voltage	$V_{(BR)DSS}$	$V_{GS}=0\text{ V}$, $I_D=250\text{ }\mu\text{A}$	500	-	-	V
Gate threshold voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}$, $I_D=0.25\text{ mA}$	2,5	3	3,5	
Zero gate voltage drain current	I_{DSS}	$V_{DS}=500\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=25\text{ °C}$	-	-	1	μA
		$V_{DS}=500\text{ V}$, $V_{GS}=0\text{ V}$, $T_j=150\text{ °C}$	-	10	-	
Gate-source leakage current	I_{GSS}	$V_{GS}=20\text{ V}$, $V_{DS}=0\text{ V}$	-	-	100	nA
Drain-source on-state resistance	$R_{DS(on)}$	$V_{GS}=10\text{ V}$, $I_D=3.8\text{ A}$, $T_j=25\text{ °C}$	-	0,47	0,52	Ω
		$V_{GS}=10\text{ V}$, $I_D=3.8\text{ A}$, $T_j=150\text{ °C}$	-	1,2	-	
Gate resistance	R_G	$f=1\text{ MHz}$, open drain	-	2,2	-	Ω

Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Dynamic characteristics						
Input capacitance	C_{iss}	$V_{GS}=0\text{ V}, V_{DS}=100\text{ V},$ $f=1\text{ MHz}$	-	680	-	pF
Output capacitance	C_{oss}		-	31	-	
Effective output capacitance, energy related ⁶⁾	$C_{o(er)}$	$V_{GS}=0\text{ V}, V_{DS}=0\text{ V}$ to 400 V	-	29	-	
Effective output capacitance, time related ⁷⁾	$C_{o(tr)}$		-	63	-	
Turn-on delay time	$t_{d(on)}$	$V_{DD}=400\text{ V},$ $V_{GS}=10\text{ V}, I_D=3.8\text{ A},$ $R_G=48.3\ \Omega$	-	35	-	ns
Rise time	t_r		-	14	-	
Turn-off delay time	$t_{d(off)}$		-	80	-	
Fall time	t_f		-	17	-	
Gate Charge Characteristics						
Gate to source charge	Q_{gs}	$V_{DD}=400\text{ V}, I_D=3.8\text{ A},$ $V_{GS}=0\text{ to }10\text{ V}$	-	3	-	nC
Gate to drain charge	Q_{gd}		-	5	-	
Gate charge total	Q_g		-	13	17	
Gate plateau voltage	$V_{plateau}$		-	5,2	-	V
Reverse Diode						
Diode forward voltage	V_{SD}	$V_{GS}=0\text{ V}, I_F=3.8\text{ A},$ $T_j=25\text{ }^\circ\text{C}$	-	0,9	1,2	V
Reverse recovery time	t_{rr}	$V_R=400\text{ V}, I_F=I_S,$ $di_F/dt=100\text{ A}/\mu\text{s}$	-	240	-	ns
Reverse recovery charge	Q_{rr}		-	1,6	-	μC
Peak reverse recovery current	I_{rrm}		-	13	-	A

²⁾ Pulse width t_p limited by $T_{j,max}$

³⁾ Repetitive avalanche causes additional power losses that can be calculated as $P_{AV}=E_{AR} \cdot f$.

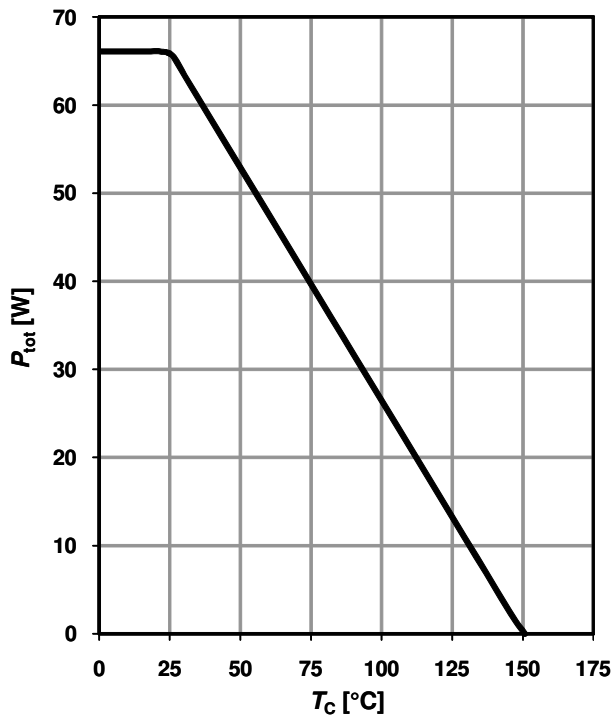
⁴⁾ $I_{SD} \leq I_D, di/dt \leq 400\text{ A}/\mu\text{s}, V_{DClink}=400\text{ V}, V_{peak} < V_{(BR)DSS}, T_j < T_{j,max}$, identical low and high side switch

⁵⁾ $C_{o(er)}$ is a fixed capacitance that gives the same stored energy as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

⁶⁾ $C_{o(tr)}$ is a fixed capacitance that gives the same charging time as C_{oss} while V_{DS} is rising from 0 to 80% V_{DSS} .

1 Power dissipation

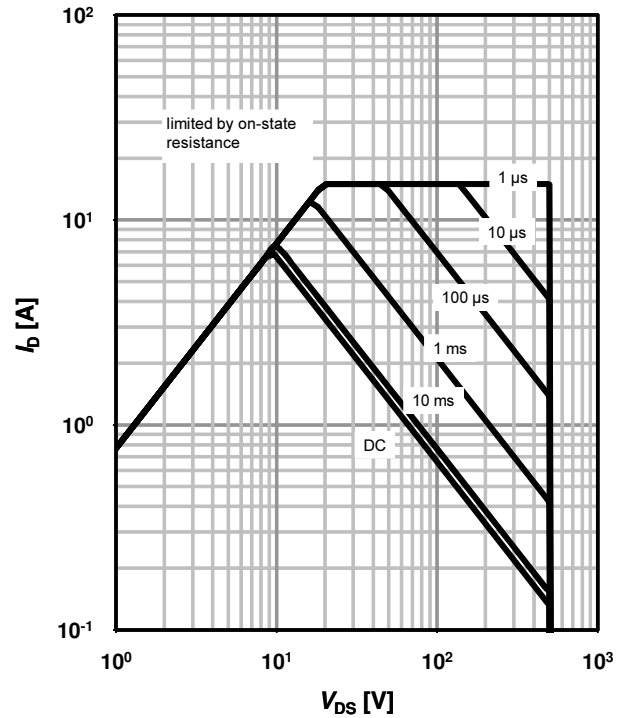
$$P_{\text{tot}} = f(T_C)$$



2 Safe operating area

$$I_D = f(V_{DS}); T_C = 25^\circ\text{C}; D = 0$$

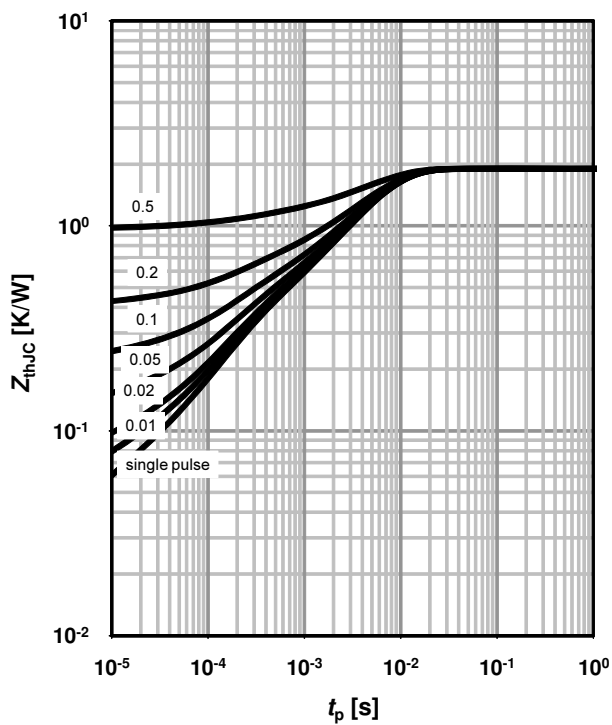
parameter: t_p



3 Max. transient thermal impedance

$$Z_{\text{th(JC)}} = f(t_p)$$

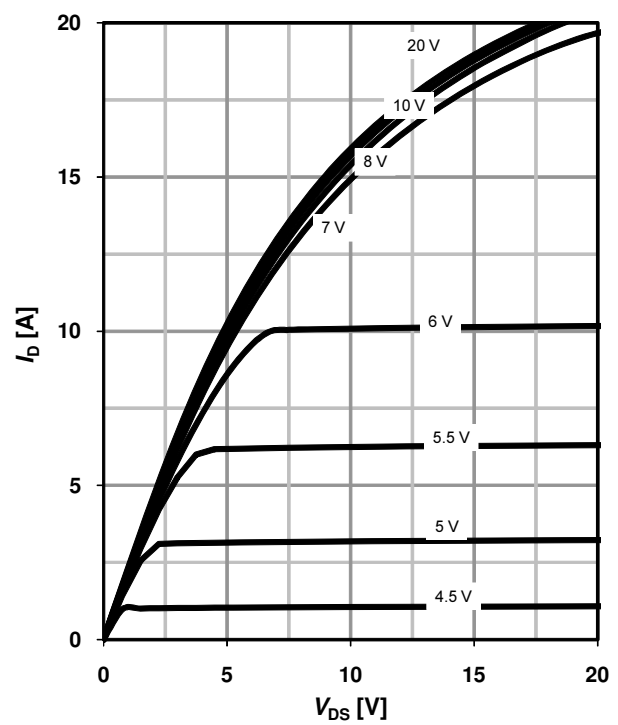
parameter: $D = t_p / T$



4 Typ. output characteristics

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

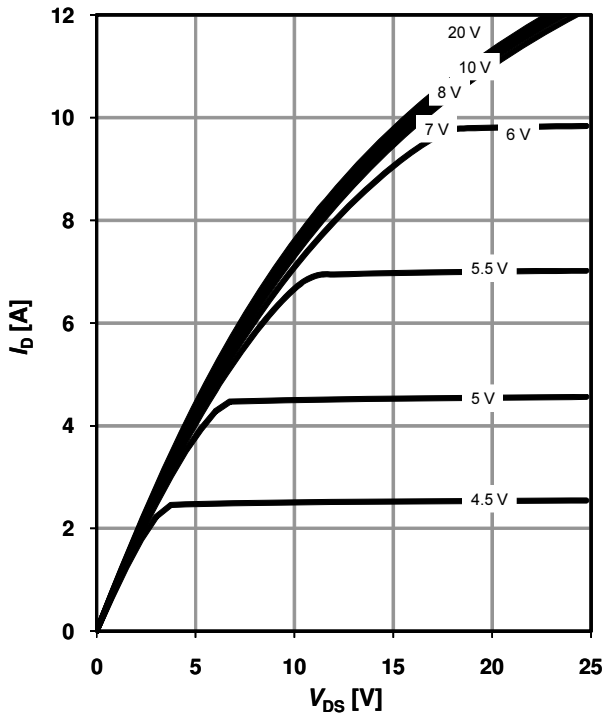
parameter: V_{GS}



5 Typ. output characteristics

$I_D = f(V_{DS}); T_j = 150\text{ °C}$

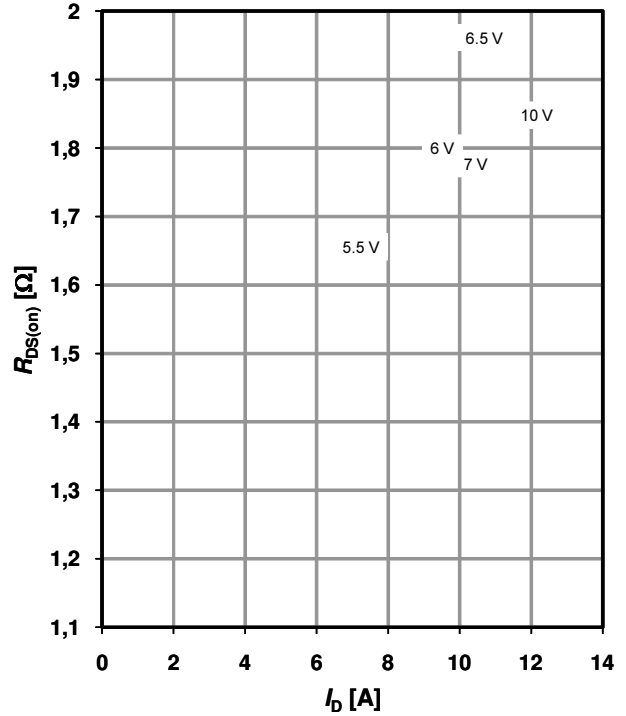
parameter: V_{GS}



6 Typ. drain-source on-state resistance

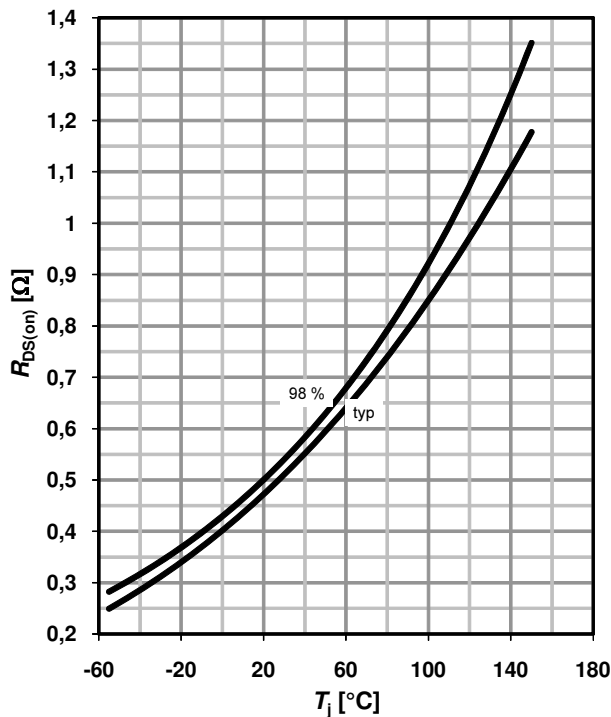
$R_{DS(on)} = f(I_D); T_j = 150\text{ °C}$

parameter: V_{GS}



7 Drain-source on-state resistance

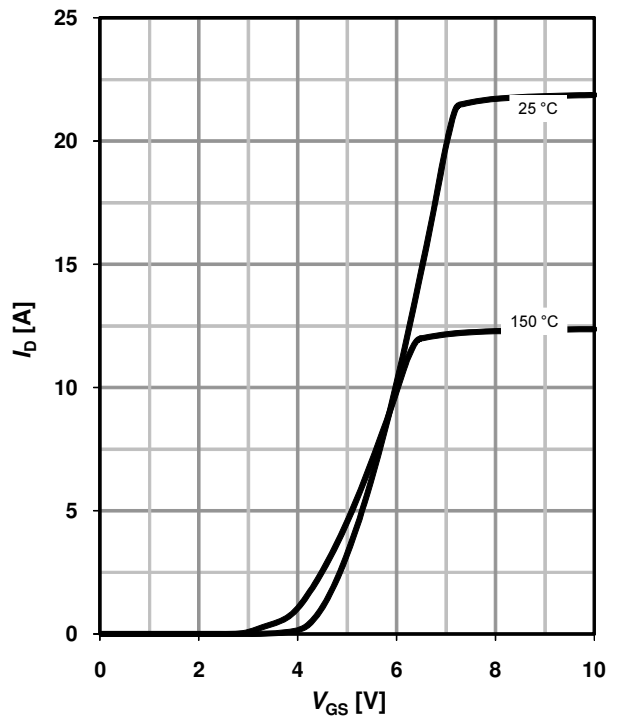
$R_{DS(on)} = f(T_j); I_D = 3.8\text{ A}; V_{GS} = 10\text{ V}$



8 Typ. transfer characteristics

$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$

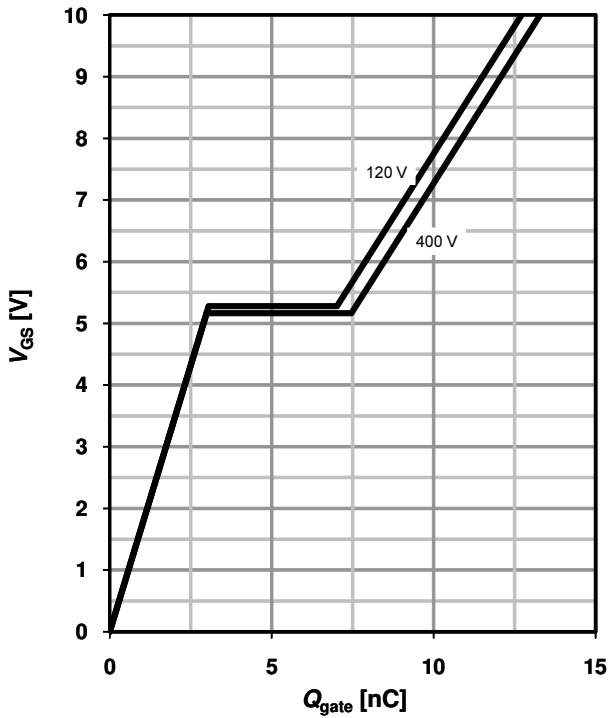
parameter: T_j



9 Typ. gate charge

$V_{GS}=f(Q_{gate}); I_D=3.8\text{ A pulsed}$

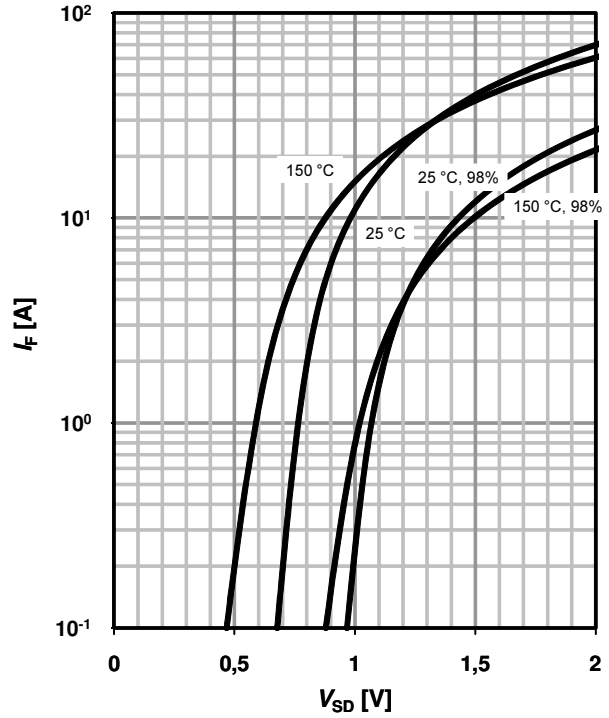
parameter: V_{DD}



10 Forward characteristics of reverse diode

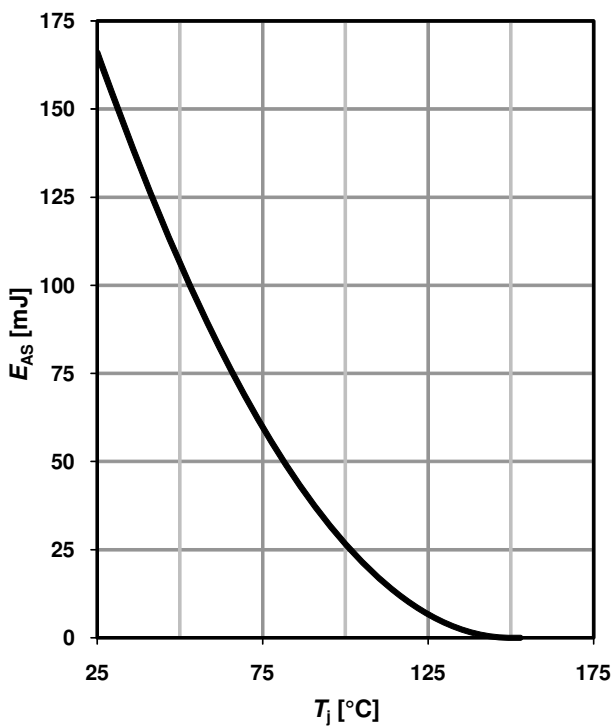
$I_F=f(V_{SD})$

parameter: T_j



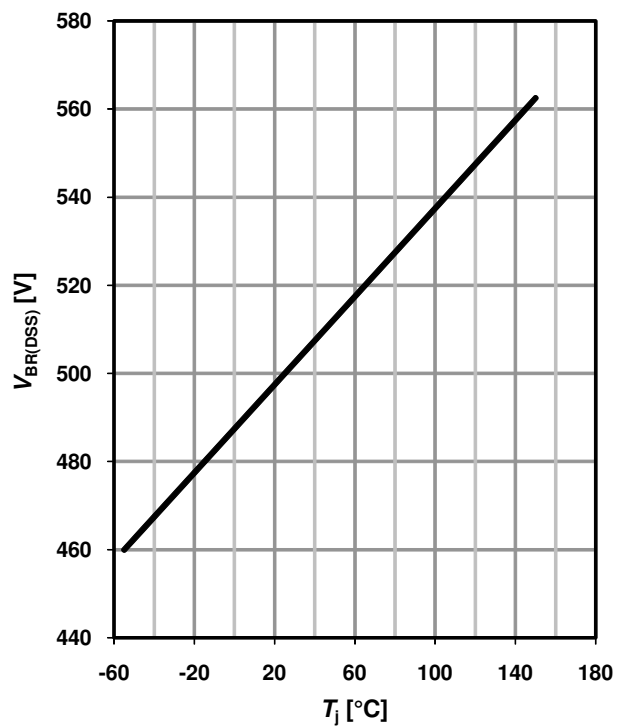
11 Avalanche energy

$E_{AS}=f(T_j); I_D=2.5\text{ A}; V_{DD}=50\text{ V}$



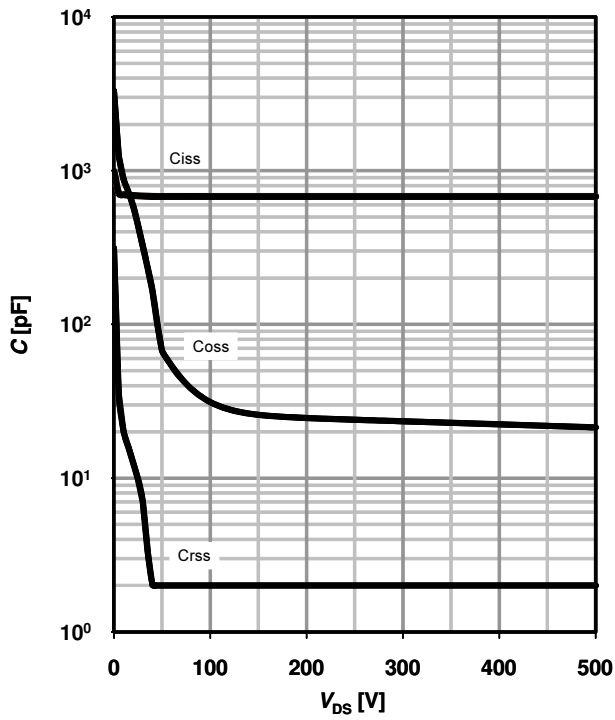
12 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=0.25\text{ mA}$



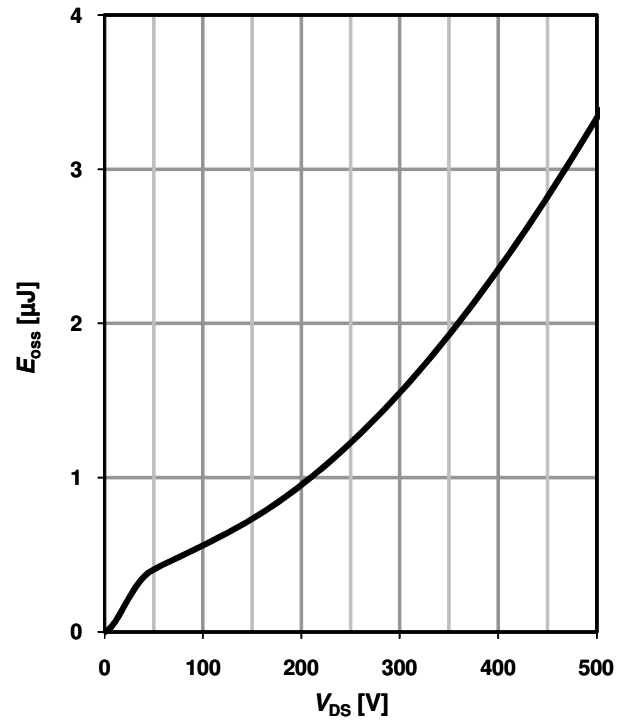
13 Typ. capacitances

$C=f(V_{DS}); V_{GS}=0\text{ V}; f=1\text{ MHz}$

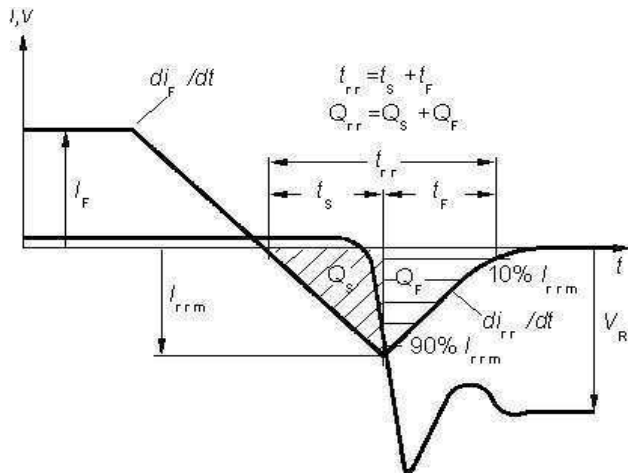


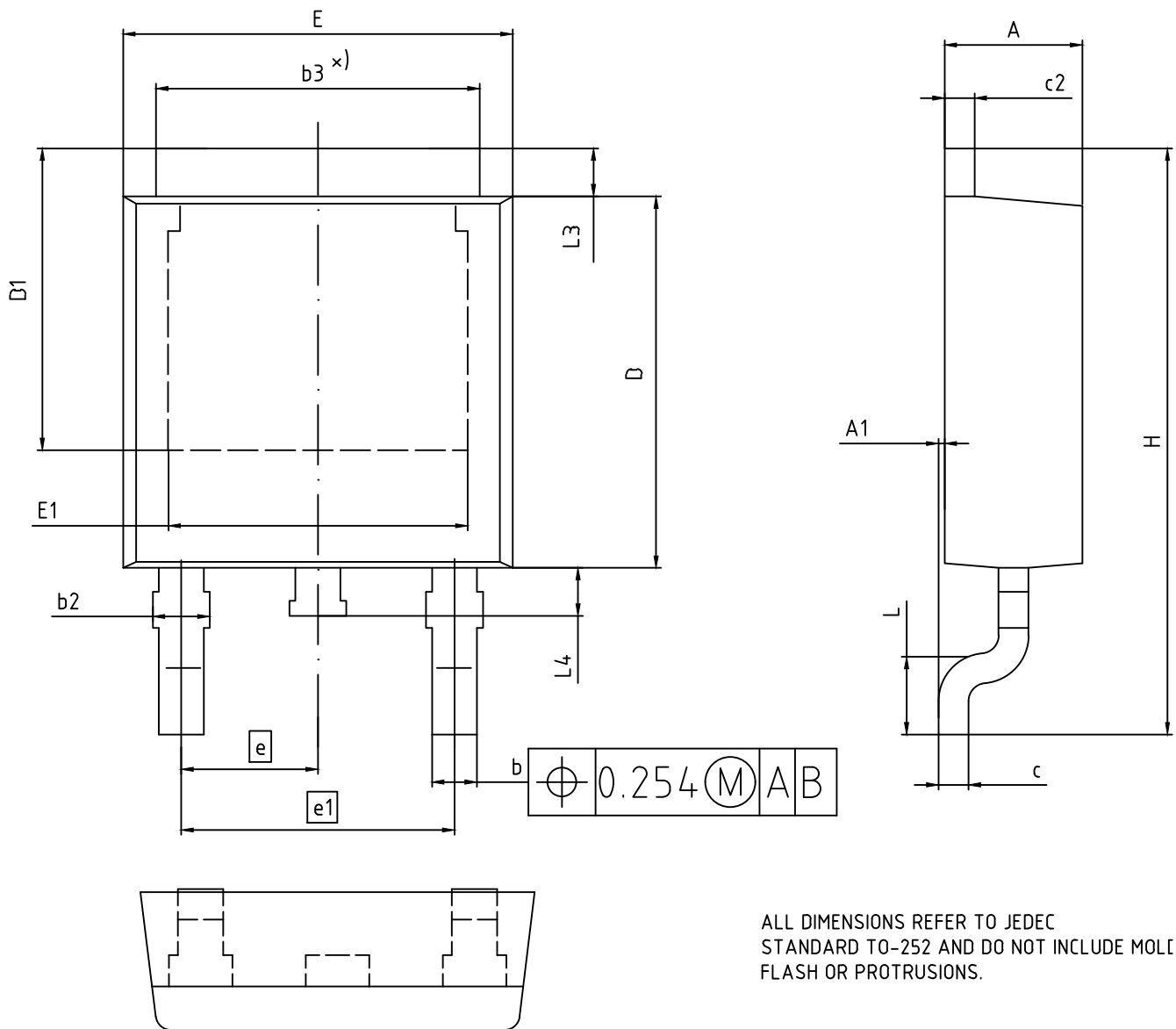
14 Typ. Coss stored energy

$E_{oss}=f(V_{DS})$



Definition of diode switching characteristics





ALL DIMENSIONS REFER TO JEDEC STANDARD TO-252 AND DO NOT INCLUDE MOLD FLASH OR PROTRUSIONS.

DIMENSION	MILLIMETERS	
	MIN.	MAX.
A	2.16	2.41
A1	0.00	0.15
b	0.64	0.89
b2	0.65	1.15
b3	4.95	5.50
c	0.46	0.61
c2	0.40	0.98
D	5.97	6.22
D1	5.02	5.84
E	6.35	6.73
E1	4.32	5.50
e	2.29	
e1	4.57	
N	3	
H	9.40	10.48
L	1.18	1.78
L3	0.89	1.27
L4	0.51	1.02

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Revision History

IPD50R520CP

Revision: 2020-05-26, Rev. 2.3

Previous Revision

Revision	Date	Subjects (major changes since last revision)
2.2	2017-07-25	Revised package drawing on page 9
2.3	2020-05-26	Update package outline

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